

Title (en)
Semiconductor device and method of fabricating the same

Title (de)
Halbleiterbauelement und Herstellungsverfahren dafür

Title (fr)
Dispositif de semi-conducteur et son procédé de fabrication

Publication
EP 2843706 A3 20160224 (EN)

Application
EP 14178402 A 20140724

Priority
KR 20130105691 A 20130903

Abstract (en)
[origin: EP2843706A2] The present disclosure relates to a semiconductor device including an oxygen gettering layer between a group III-V compound semiconductor layer and a dielectric layer, and a method of fabricating the semiconductor device. The semiconductor device may include a compound semiconductor layer; a dielectric layer disposed on the compound semiconductor layer; and an oxygen gettering layer interposed between the compound semiconductor layer and the dielectric layer. The oxygen gettering layer includes a material having a higher oxygen affinity than a material of the compound semiconductor layer.

IPC 8 full level
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H01L 21/28264 (2013.01 - CN EP US); **H01L 21/322** (2013.01 - US); **H01L 21/3228** (2013.01 - US); **H01L 29/20** (2013.01 - CN EP US); **H01L 29/34** (2013.01 - US); **H01L 29/513** (2013.01 - CN EP US); **H01L 29/66522** (2013.01 - CN EP US); **H01L 29/7851** (2013.01 - EP US); **H01L 31/0256** (2013.01 - KR); **H01L 31/04** (2013.01 - KR); **H01L 31/18** (2013.01 - KR); **H01L 21/02175** (2013.01 - US); **H01L 21/02189** (2013.01 - US); **H01L 21/02192** (2013.01 - US); **H01L 21/022** (2013.01 - US); **H01L 21/02304** (2013.01 - US); **H01L 21/28158** (2013.01 - US); **H01L 29/2003** (2013.01 - CN EP US); **H01L 29/24** (2013.01 - CN EP US); **H01L 29/517** (2013.01 - CN EP US); **H01L 29/518** (2013.01 - CN EP US); **Y02E 10/50** (2013.01 - EP)

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Designated contracting state (EPC)
AL AT BE BG CH CY CZ DE DK EE ES FI FR GB GR HR HU IE IS IT LI LT LU LV MC MK MT NL NO PL PT RO RS SE SI SK SM TR

Designated extension state (EPC)

BA ME

DOCDB simple family (publication)

EP 2843706 A2 20150304; EP 2843706 A3 20160224; EP 2843706 B1 20190306; CN 104425620 A 20150318; CN 104425620 B 20200821;
KR 102099881 B1 20200515; KR 20150026610 A 20150311; US 2015061088 A1 20150305; US 2016172450 A1 20160616;
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